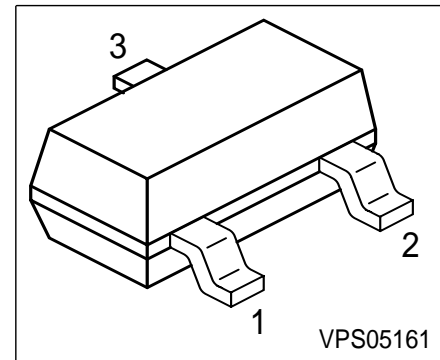


**NPN Silicon RF Transistor**

- For low noise, low-power amplifiers in mobile communications systems (pager, cordless telephone) at collector currents from 0.2 mA to 8 mA
- $f_T = 7.5$  GHz  
 $F = 1.5$  dB at 900 MHz



**ESD: Electrostatic discharge sensitive device, observe handling precaution!**

Type	Marking	Pin Configuration			Package
BFR280	REs	1 = B	2 = E	3 = C	SOT23

**Maximum Ratings**

Parameter	Symbol	Value	Unit
Collector-emitter voltage	$V_{CEO}$	8	V
Collector-emitter voltage	$V_{CES}$	10	
Collector-base voltage	$V_{CBO}$	10	
Emitter-base voltage	$V_{EBO}$	2	
Collector current	$I_C$	10	mA
Base current	$I_B$	1.2	
Total power dissipation $T_S \leq 116$ °C <sup>1)</sup>	$P_{tot}$	80	mW
Junction temperature	$T_j$	150	°C
Ambient temperature	$T_A$	-65 ... 150	
Storage temperature	$T_{stg}$	-65 ... 150	

**Thermal Resistance**

Junction - soldering point <sup>2)</sup>	$R_{thJS}$	$\leq 425$	K/W
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<sup>1)</sup>  $T_S$  is measured on the collector lead at the soldering point to the pcb

<sup>2)</sup> For calculation of  $R_{thJA}$  please refer to Application Note Thermal Resistance

**Electrical Characteristics** at  $T_A = 25^\circ\text{C}$ , unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>DC characteristics</b>					
Collector-emitter breakdown voltage $I_C = 1 \text{ mA}, I_B = 0$	$V_{(BR)CEO}$	8	-	-	V
Collector-emitter cutoff current $V_{CE} = 10 \text{ V}, V_{BE} = 0$	$I_{CES}$	-	-	100	$\mu\text{A}$
Collector-base cutoff current $V_{CB} = 8 \text{ V}, I_E = 0$	$I_{CBO}$	-	-	100	nA
Emitter-base cutoff current $V_{EB} = 1 \text{ V}, I_C = 0$	$I_{EBO}$	-	-	1	$\mu\text{A}$
DC current gain $I_C = 3 \text{ mA}, V_{CE} = 5 \text{ V}$	$h_{FE}$	30	100	200	-

**Electrical Characteristics** at  $T_A = 25^\circ\text{C}$ , unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>AC characteristics</b> (verified by random sampling)					
Transition frequency $I_C = 6 \text{ mA}$ , $V_{CE} = 5 \text{ V}$ , $f = 500 \text{ MHz}$	$f_T$	5	7.5	-	GHz
Collector-base capacitance $V_{CB} = 5 \text{ V}$ , $f = 1 \text{ MHz}$	$C_{cb}$	-	0.27	0.45	pF
Collector-emitter capacitance $V_{CE} = 5 \text{ V}$ , $f = 1 \text{ MHz}$	$C_{ce}$	-	0.18	-	
Emitter-base capacitance $V_{EB} = 0.5 \text{ V}$ , $f = 1 \text{ MHz}$	$C_{eb}$	-	0.22	-	
Noise figure $I_C = 1.5 \text{ mA}$ , $V_{CE} = 5 \text{ V}$ , $Z_S = Z_{\text{Sopt}}$ , $f = 900 \text{ MHz}$ $f = 1.8 \text{ GHz}$	$F$	-	1.5 2	-	dB
Power gain, maximum stable 1) $I_C = 3 \text{ mA}$ , $V_{CE} = 5 \text{ V}$ , $Z_S = Z_{\text{Sopt}}$ , $Z_L = Z_{\text{Lopt}}$ , $f = 900 \text{ MHz}$ $f = 1.8 \text{ GHz}$	$G_{ms}$	-	17 11.5	-	
Transducer gain $I_C = 3 \text{ mA}$ , $V_{CE} = 5 \text{ V}$ , $Z_S = Z_L = 50\Omega$ , $f = 900 \text{ MHz}$ $f = 1.8 \text{ GHz}$	$ S_{21e} ^2$	-	13 8	-	
		-		-	

$$^1G_{ms} = |S_{21} / S_{12}|$$

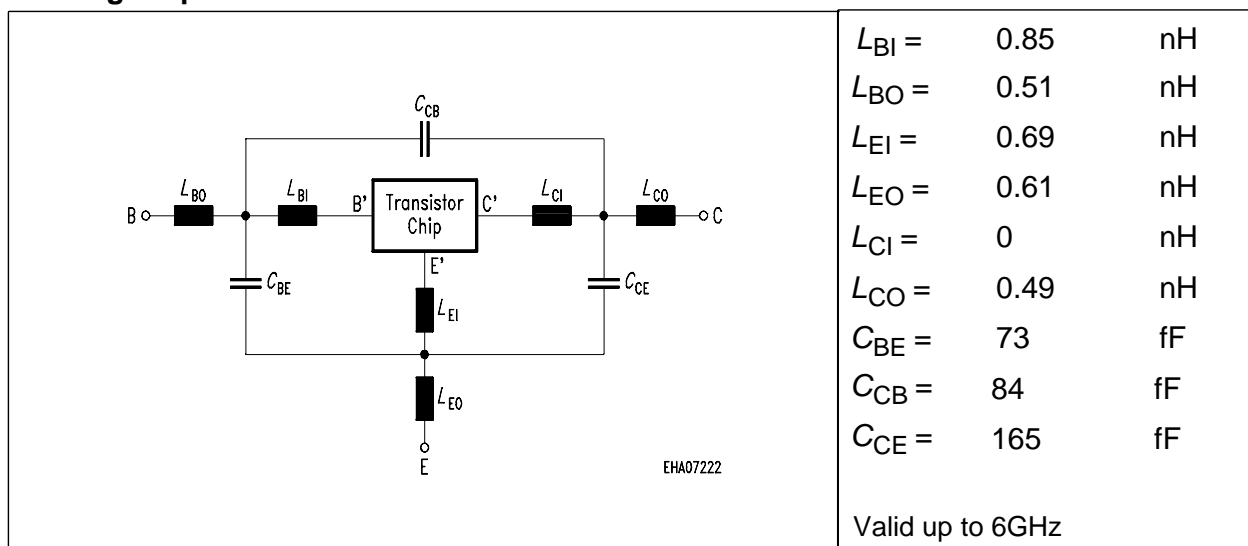
**SPICE Parameters (Gummel-Poon Model, Berkley-SPICE 2G.6 Syntax) :**
**Transistor Chip Data**

IS =	6.472	fA	BF =	89.888	-	NF =	1.0801	-
VAF =	25.609	V	IKF =	0.073457	A	ISE =	15.596	fA
NE =	1.6163	-	BR =	20.238	-	NR =	0.83403	-
VAR =	5.6909	V	IKR =	0.012696	A	ISC =	1.409	fA
NC =	1.0651	-	RB =	15	$\Omega$	IRB =	0.031958	mA
RBM =	14.999	$\Omega$	RE =	2.4518		RC =	6.989	$\Omega$
CJE =	36.218	fF	VJE =	0.70035	V	MJE =	0.69773	-
TF =	11.744	ps	XTF =	0.21585	-	VTF =	0.2035	V
ITF =	6.2179	mA	PTF =	0	deg	CJC =	252.99	fF
VJC =	1.1943	V	MJC =	0.30017	-	XCJC =	0.19188	-
TR =	2.3693	ns	CJS =	0	fF	VJS =	0.75	V
MJS =	0	-	XTB =	0	-	EG =	1.11	eV
XTI =	3	-	FC =	0.96275	-	TNOM	300	K

All parameters are ready to use, no scaling is necessary.

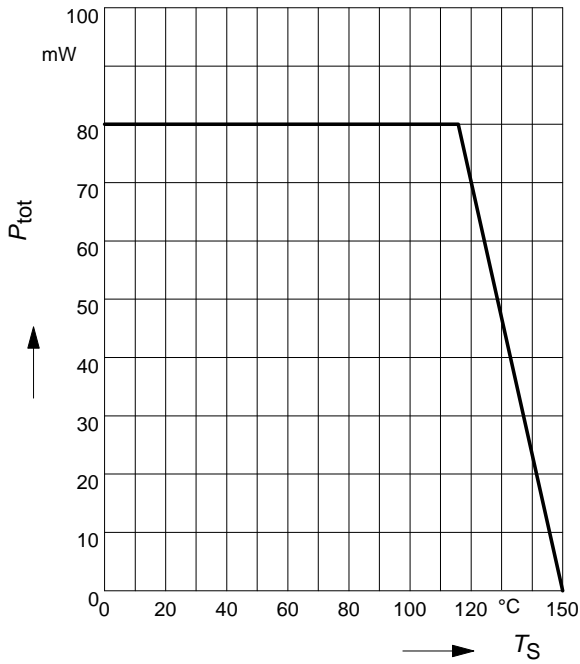
Extracted on behalf of Infineon Technologies AG by:

Institut für Mobil-und Satellitentechnik (IMST)

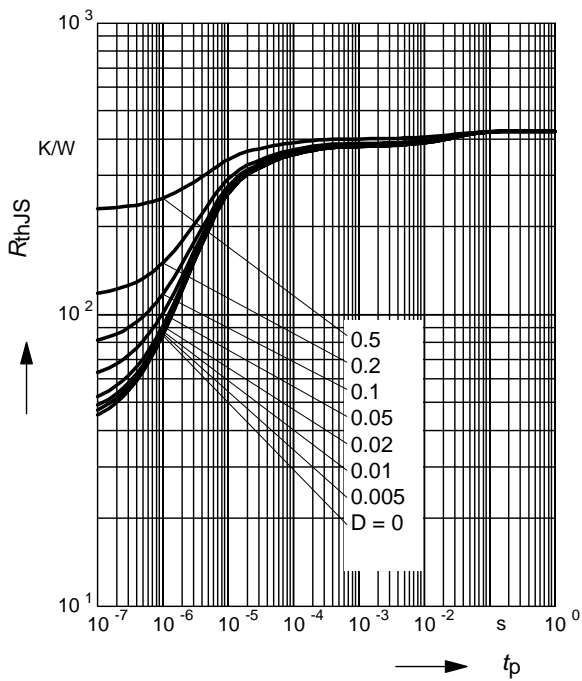
**Package Equivalent Circuit:**


For examples and ready to use parameters please contact your local Infineon Technologies distributor or sales office to obtain a Infineon Technologies CD-ROM or see Internet: <http://www.infineon.com/products/discrete/index.htm>

**Total power dissipation  $P_{tot} = f(T_S)$**

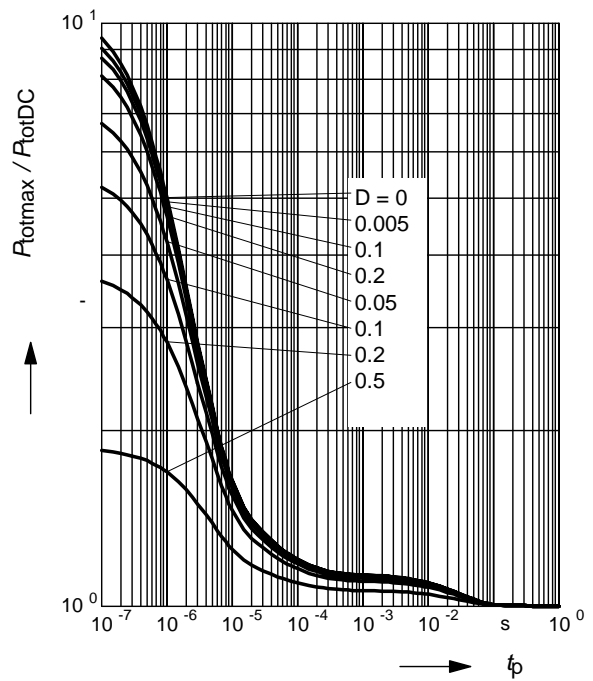


**Permissible Pulse Load  $R_{thJS} = f(t_p)$**



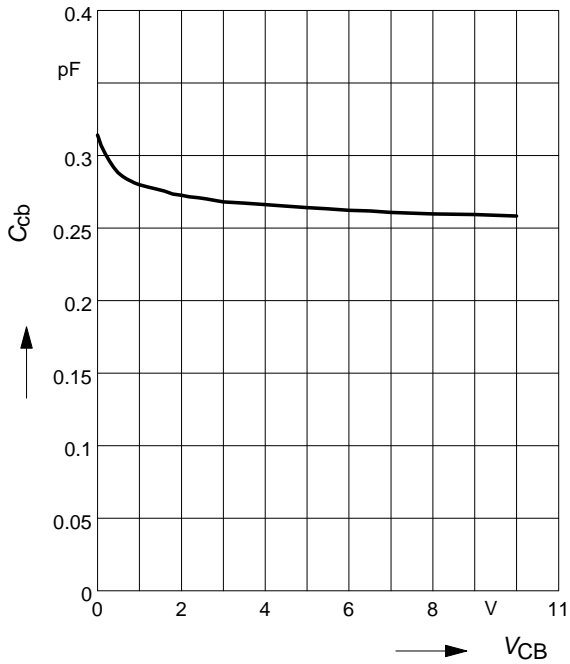
**Permissible Pulse Load**

$P_{totmax}/P_{totDC} = f(t_p)$



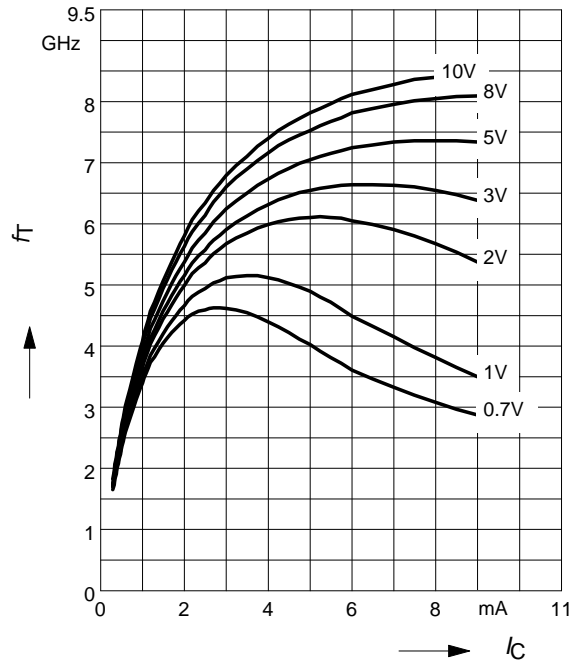
**Collector-base capacitance**  $C_{cb} = f(V_{CB})$

$f = 1\text{MHz}$



**Transition frequency**  $f_T = f(I_C)$

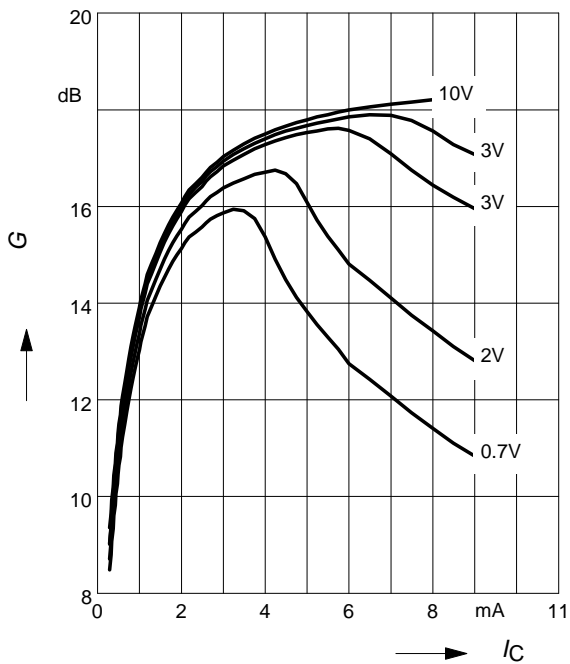
$V_{CE} = \text{Parameter}$



**Power Gain**  $G_{ma}, G_{ms} = f(I_C)$

$f = 0.9\text{GHz}$

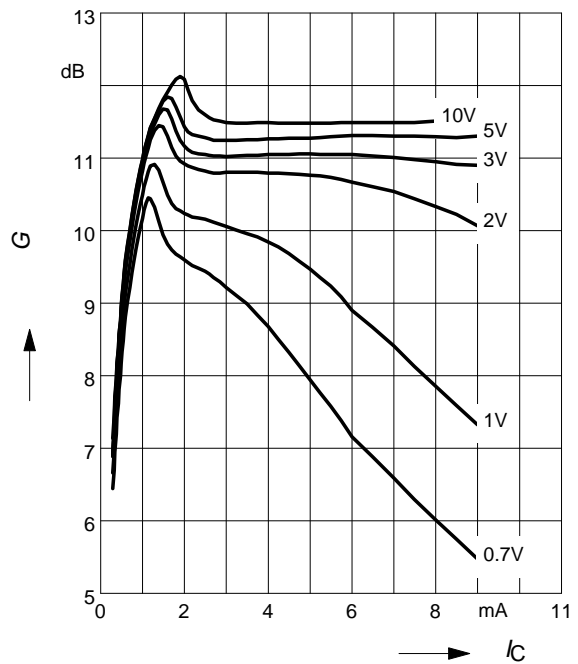
$V_{CE} = \text{Parameter}$



**Power Gain**  $G_{ma}, G_{ms} = f(I_C)$

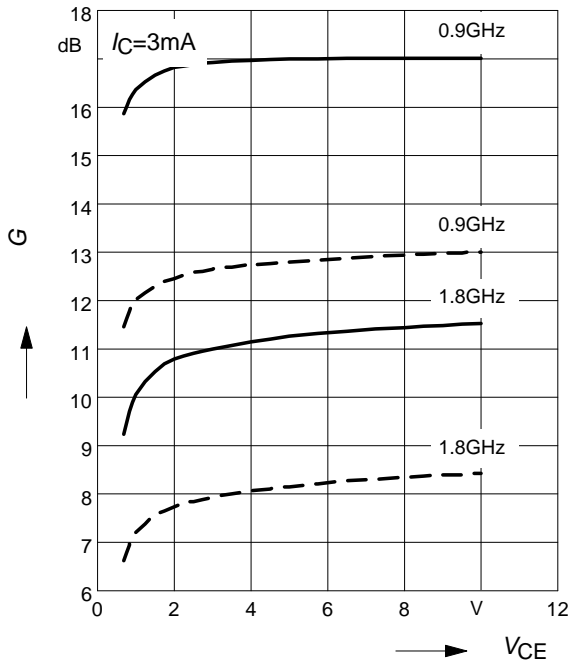
$f = 1.8\text{GHz}$

$V_{CE} = \text{Parameter}$



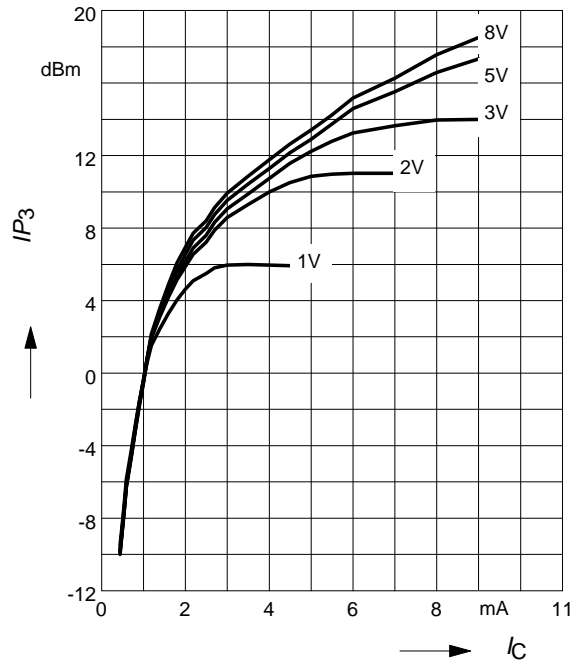
**Power Gain**  $G_{ma}$ ,  $G_{ms} = f(V_{CE})$ : \_\_\_\_\_  
 $|S_{21}|^2 = f(V_{CE})$ : -----

$f$  = Parameter



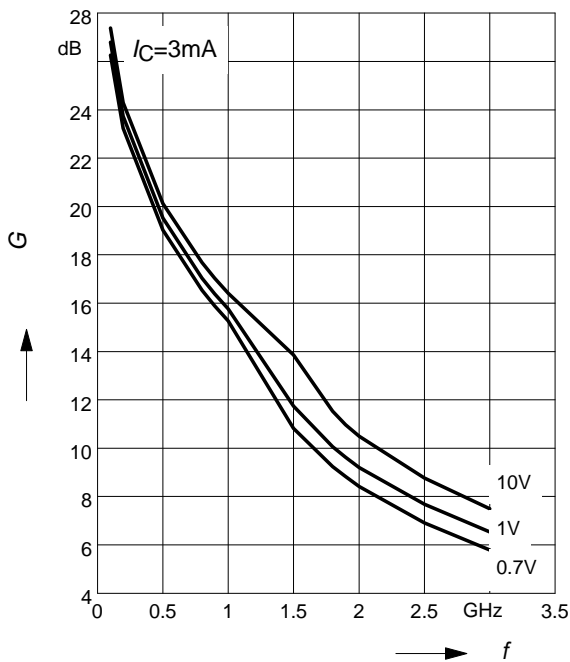
**Intermodulation Intercept Point**  $IP_3 = f(I_C)$   
 (3rd order, Output,  $Z_S = Z_L = 50\Omega$ )

$V_{CE}$  = Parameter,  $f = 900MHz$



**Power Gain**  $G_{ma}$ ,  $G_{ms} = f(f)$

$V_{CE}$  = Parameter



**Power Gain**  $|S_{21}|^2 = f(f)$

$V_{CE}$  = Parameter

